

#### ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises a gate insulation film 23 formed on a first region 14 of a semiconductor substrate 10 and including a silicon oxide-based insulation film 18, a high dielectric constant film 20 formed on the silicon oxide-based insulation film 18, and an oxygen diffusion preventing film 22 formed on the high dielectric constant film 18 and having a lower oxygen diffusion coefficient than the high dielectric constant film 18; a gate electrode 24 formed on the first gate insulation film 23; a gate insulation film 25 formed on a second region 16 of the semiconductor substrate 10 and including the high dielectric constant film 20 and the oxygen diffusion preventing film 22 formed on the high dielectric constant film 20; and a gate electrode 24 formed on the gate insulation film 26.